

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	FDD6637
▶ Overseas	Part Number	FDD6637
▶ Equivalent	Part Number	FDD6637

EV is the abbreviation of name EVVO

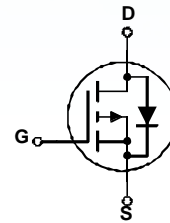
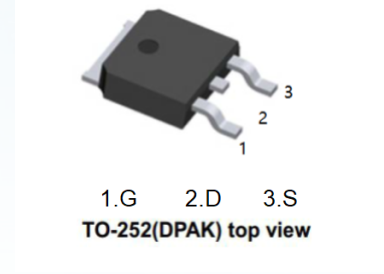
-30V P-Channel MOSFET

Applications

- Inverter
- Power Supplies

Features

- $V_{DSS} = -30V$
- $R_{DS(ON)} = 11.6m\Omega (V_{GS} = -10 V)$
- $R_{DS(ON)} = 18m\Omega (V_{GS} = -4.5 V)$
- High performance trench technology for extremely low $R_{DS(ON)}$
- RoHS Compliant



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	-30	V
$V_{DS(Avalanche)}$	Drain-Source Avalanche Voltage (maximum) (Note 4)	-40	V
V_{GSS}	Gate-Source Voltage	± 25	V
I_D	Continuous Drain Current @ $T_C=25^\circ C$ (Note 3)	@ $T_A=25^\circ C$ (Note 1a)	-55
		Pulsed (Note 1a)	-13
			-100
P_D	Power Dissipation @ $T_C=25^\circ C$ (Note 3)	@ $T_A=25^\circ C$ (Note 1a)	57
		@ $T_A=25^\circ C$ (Note 1b)	3.1
			1.3
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	2.2	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	40	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	96	

-30V P-Channel MOSFET
Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
E_{AS}	Drain-Source Avalanche Energy (Single Pulse)	$V_{DD} = -35\text{ V}$, $I_D = -11\text{ A}$, $L=1\text{mH}$		61		mJ
I_{AS}	Drain-Source Avalanche Current			-14		A
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_D = -250\ \mu\text{A}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -28\text{ V}$, $V_{GS} = 0\text{ V}$			-1	μA
I_{GSS}	Gate-Body Leakage	$V_{GS} = \pm 25\text{ V}$, $V_{DS} = 0\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$	-1	-1.6	-3	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}$, $I_D = -14\text{ A}$ $V_{GS} = -4.5\text{ V}$, $I_D = -11\text{ A}$		9.7 14.4	11.6 18	m Ω
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{ V}$, $I_D = -14\text{ A}$		35		S
C_{iss}	Input Capacitance	$V_{DS} = -20\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1.0\text{ MHz}$		2370		pF
C_{oss}	Output Capacitance			470		pF
C_{rss}	Reverse Transfer Capacitance			250		pF
R_G	Gate Resistance	$f = 1.0\text{ MHz}$		3.6		Ω
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = -20\text{ V}$, $I_D = -1\text{ A}$, $V_{GS} = -10\text{ V}$, $R_{GEN} = 6\ \Omega$		18	32	ns
t_r	Turn-On Rise Time			10	20	ns
$t_{d(off)}$	Turn-Off Delay Time			62	100	ns
t_f	Turn-Off Fall Time			36	58	ns
Q_g	Total Gate Charge, $V_{GS} = -10\text{V}$	$V_{DS} = -20\text{ V}$, $I_D = -14\text{ A}$		45	63	nC
Q_g	Total Gate Charge, $V_{GS} = -5\text{V}$			25	35	nC
Q_{gs}	Gate-Source Charge			7		nC
Q_{gd}	Gate-Drain Charge			10		nC

-30V P-Channel MOSFET

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = -14\text{ A}$ (Note 2)		-0.8	-1.2	V
t_{rr}	Diode Reverse Recovery Time	$I_F = -14\text{ A}$, $diF/dt = 100\text{ A}/\mu\text{s}$		28		ns
Q_{rr}	Diode Reverse Recovery Charge			15		nC

Notes:

- $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) $R_{\theta JA} = 40^\circ\text{C}/\text{W}$ when mounted on a 1 in^2 pad of 2 oz copper



b) $R_{\theta JA} = 96^\circ\text{C}/\text{W}$ when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

- Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

- Maximum current is calculated as:
$$\sqrt{\frac{P_D}{R_{DS(ON)}}}$$

where P_D is maximum power dissipation at $T_C = 25^\circ\text{C}$ and $R_{DS(on)}$ is at $T_{J(max)}$ and $V_{GS} = 10\text{V}$. Package current limitation is 21A

- BV(avalanche) Single-Pulse rating is guaranteed if device is operated within the UIS SOA boundary of the device.

-30V P-Channel MOSFET

Typical Characteristics

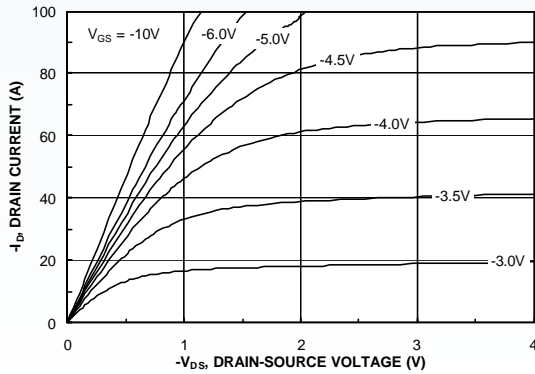


Figure 1. On-Region Characteristics

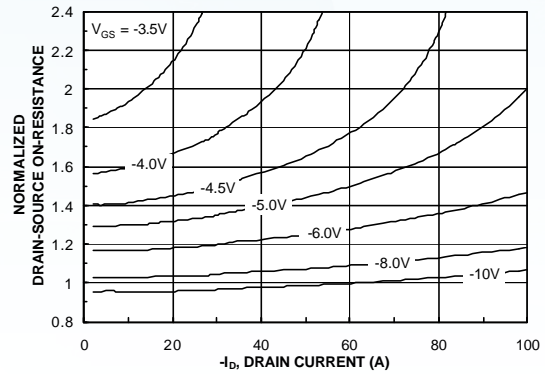


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

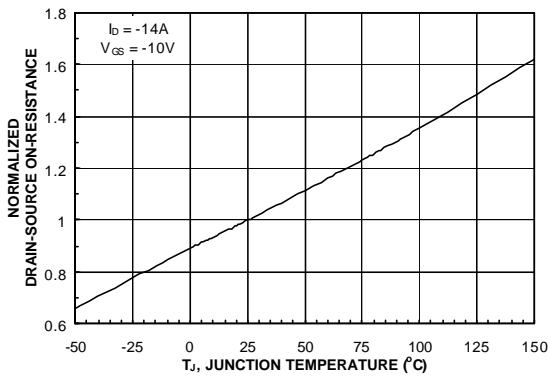


Figure 3. On-Resistance Variation with Temperature

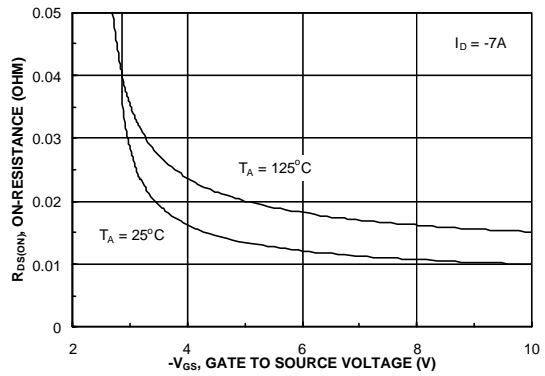


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

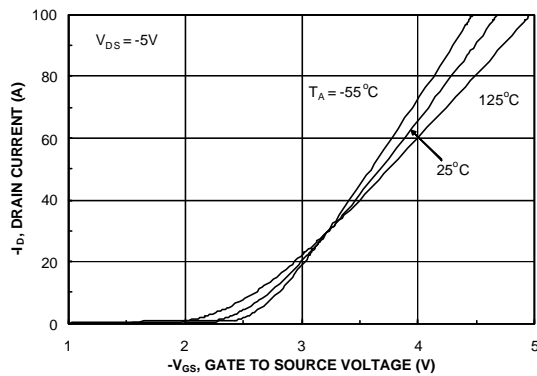


Figure 5. Transfer Characteristics

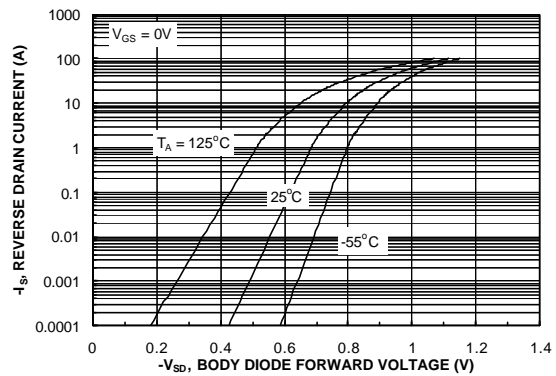


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

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Typical Characteristics

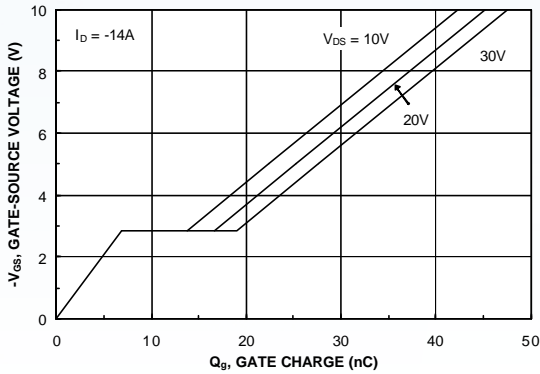


Figure 7. Gate Charge Characteristics

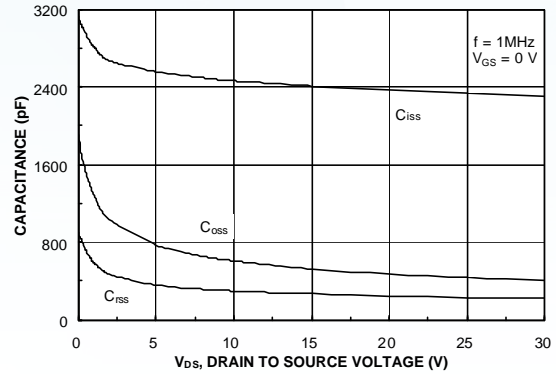


Figure 8. Capacitance Characteristics

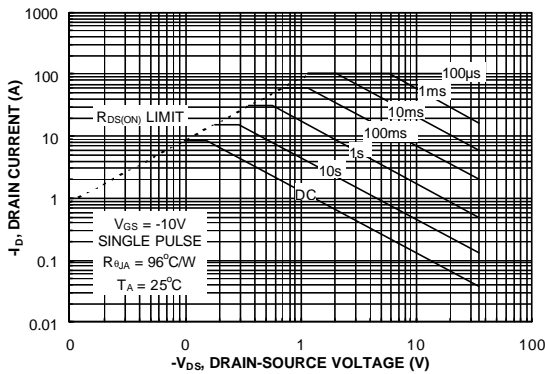


Figure 9. Maximum Safe Operating Area

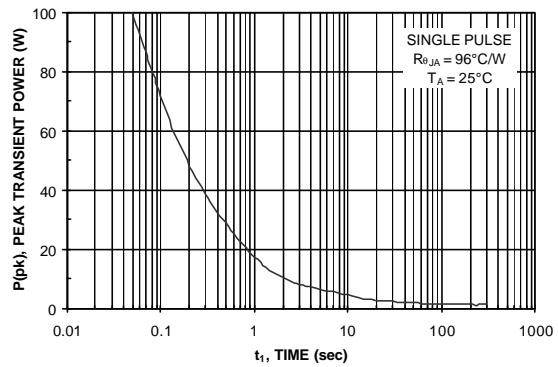


Figure 10. Single Pulse Maximum Power Dissipation

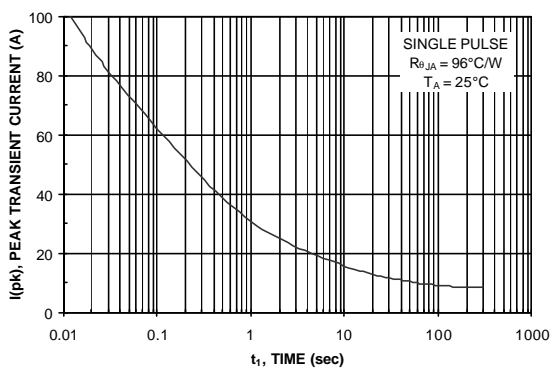


Figure 11. Single Pulse Maximum Peak Current

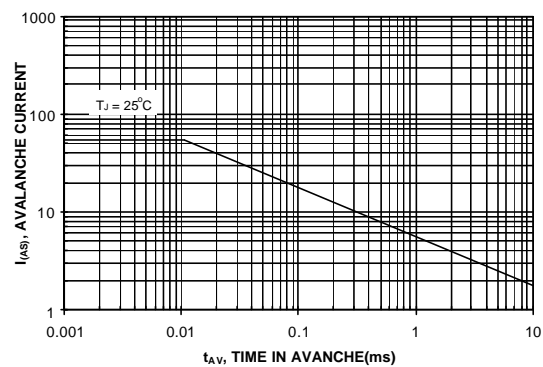


Figure 12. Unclamped Inductive Switching Capability

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Typical Characteristics

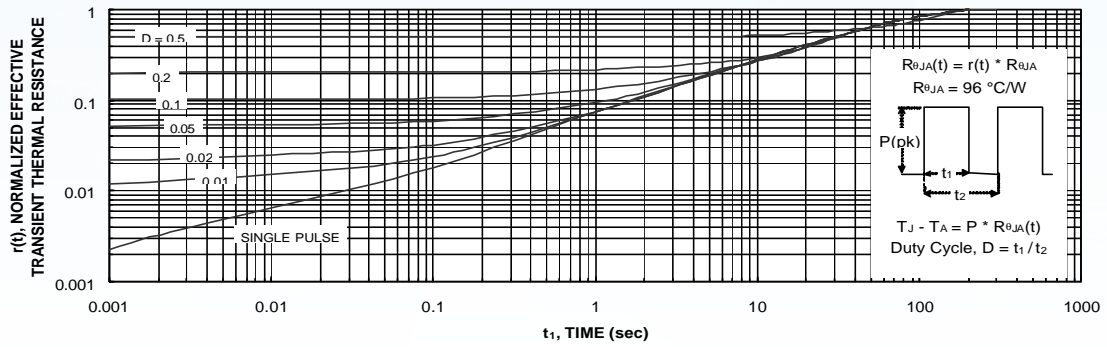


Figure 13. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

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Test Circuits and Waveforms

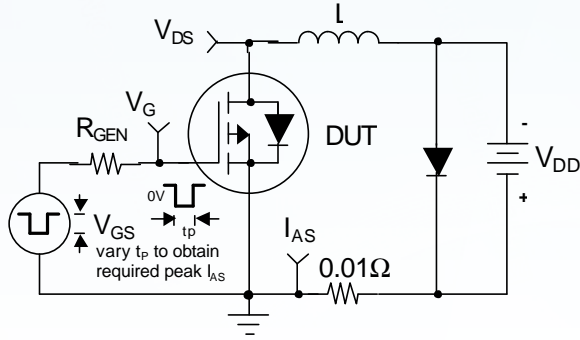


Figure 14. Unclamped Inductive Load Test Circuit

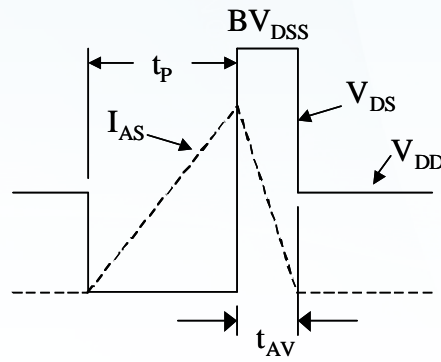


Figure 15. Unclamped Inductive Waveforms

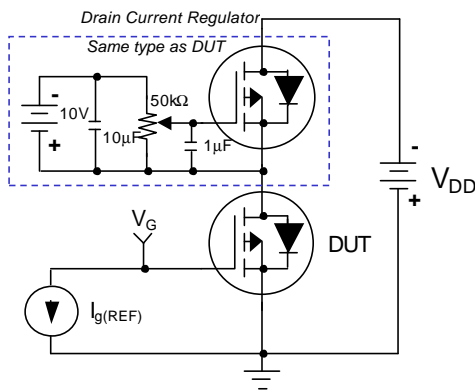


Figure 16. Gate Charge Test Circuit

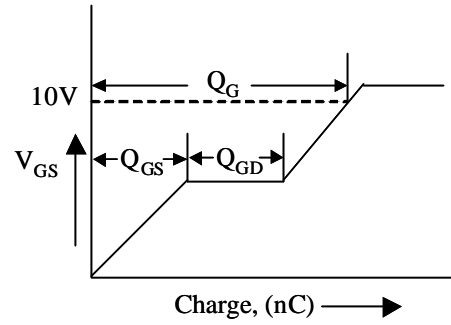


Figure 17. Gate Charge Waveform

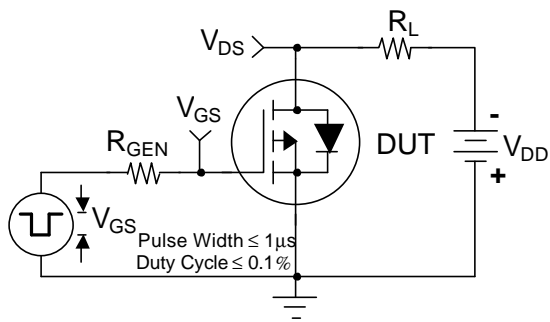


Figure 18. Switching Time Test Circuit

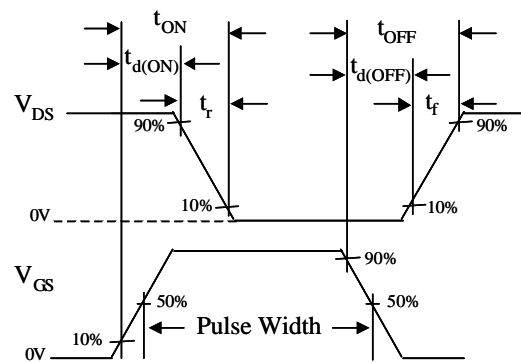
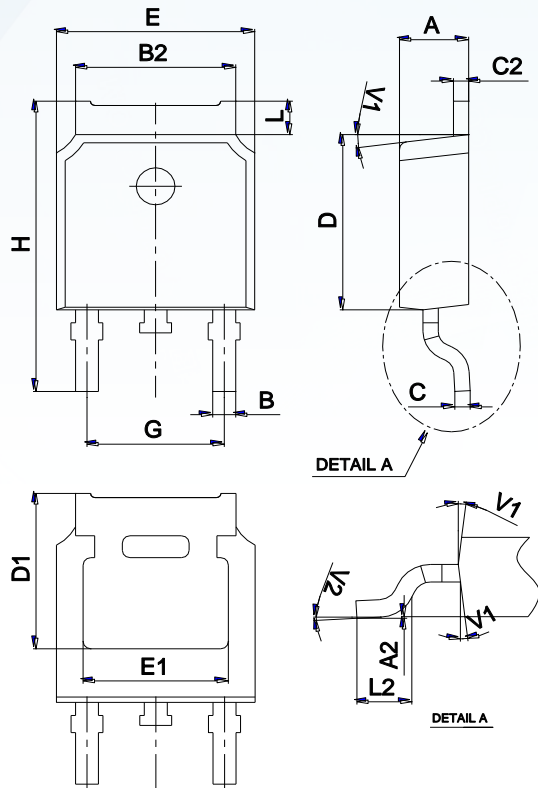


Figure 19. Switching Time Waveforms

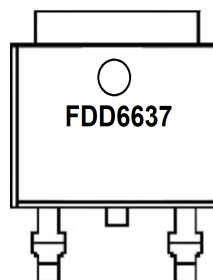
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Package Mechanical Data TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
FDD6637	TO-252	2500	Tape and reel

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